NSN 5961-01-179-3476

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-179-3476 **Inclosure Material:** Glass **Overall Length:** 0.570 inches **Terminal Length:** 1.000 inches **Overall Diameter:** 0.235 inches **Function For Which Designed:** Transient suppressor Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-13 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method: Terminal Features Provided:** Hermetically sealed case and quality assurance level txv **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 34.2 breakdown voltage, dc and 37.8 breakdown voltage, dc and 30.8 working peak reverse voltage **Current Rating Per Characteristic:** 5.00 microamperes forward current, average peak **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-prf-19500/500 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Mil-prf-19500 spec.

Mil-std (military Standard):

No Fiig: A110a0